

Isc N-Channel MOSFET Transistor

IRFI1010N

• FEATURES

- With TO-220F package
- Low input capacitance and gate charge
- Low gate input resistance
- Reduced switching and conduction losses
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

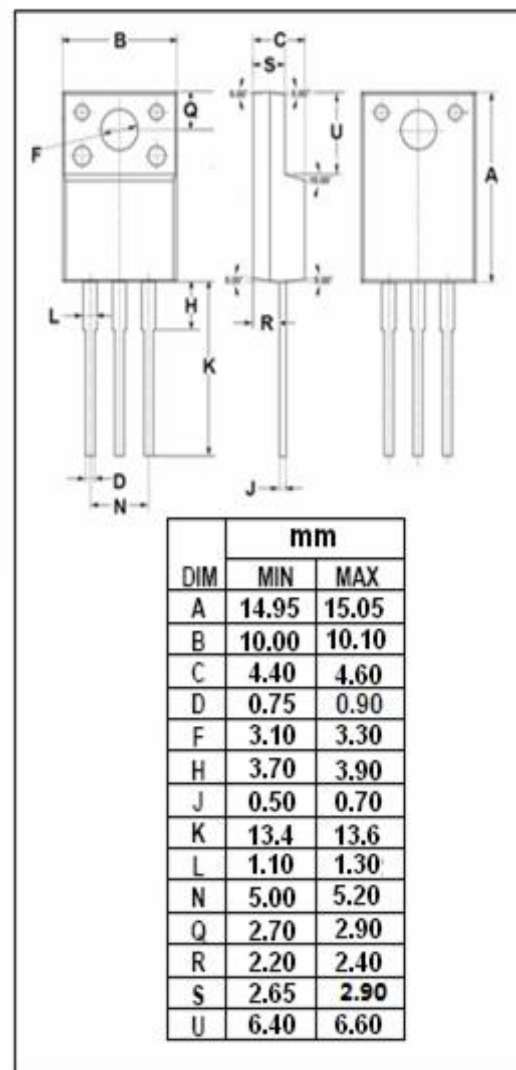
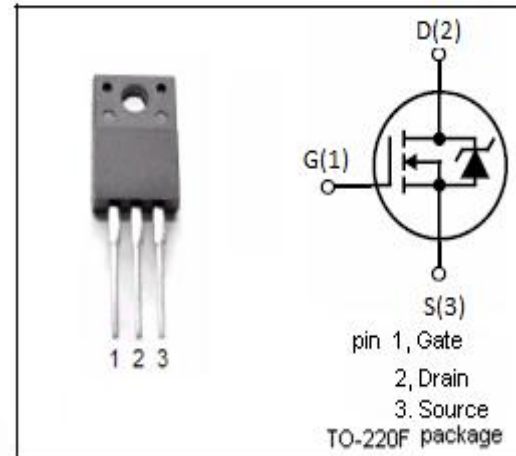
- Switching applications

• ABSOLUTE MAXIMUM RATINGS(T_a=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	55	V
V _{GSS}	Gate-Source Voltage	±20	V
I _D	Drain Current-Continuous @T _c =25°C (V _{GS} at 10V) T _c =100°C	49 35	A
I _{DM}	Drain Current-Single Pulsed	290	A
P _D	Total Dissipation @T _c =25°C	58	W
T _j	Max. Operating Junction Temperature	175	°C
T _{stg}	Storage Temperature	-55~175	°C

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th(ch-c)}	Channel-to-case thermal resistance	2.6	°C/W
R _{th(ch-a)}	Channel-to-ambient thermal resistance	65	°C/W



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ELECTRICAL CHARACTERISTICS

T_C=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V; I _D =0.25mA	55			V
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} ; I _D =0.25mA	2.0		4.0	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D =26A			12	mΩ
I _{GSS}	Gate-Source Leakage Current	V _{GS} = ±20V; V _{DS} = 0V			±0.1	μA
I _{DSS}	Drain-Source Leakage Current	V _{DS} = 55V; V _{GS} = 0V; T _j =25°C V _{DS} = 55V; V _{GS} = 0V; T _j =150°C			25 250	μA
V _{SDF}	Diode forward voltage	I _{SD} =26A, V _{GS} = 0 V			1.3	V